

Listing of the Claims :

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1-15. (Canceled)

16. (Currently amended) An epitaxial growth method of III-V nitrides alloy, comprising:

forming an initial buffer layer on a substrate;
spreading a liquid comprising one or more group III elements and nitrogen on the initial buffer layer by spinning the substrate having the liquid at selected rotation speed to form a thin, spin-coated layer covering the entire initial buffer layer on the a substrate

annealing the spin-coated layer in a gas atmosphere at a temperature equal to or higher than 700°C so as to crystallize the spin-coated layer; and

growing an III-V nitride alloy film on the spin-coated film after said annealing, which is thicker than the spin coated layer and provided that any group III element in the grown III-V nitride alloy film is different from the one or more group III elements of the spin-coated film, wherein lattice constant of the initial buffer layer is between that of the substrate and that of the overgrown III-V alloy film.

17. (Previously Presented) The epitaxial growth method of claim 16, wherein the gas atmosphere comprises nitrogen as an element.

18. (Canceled)

19. (Previously Presented) The epitaxial growth method of claim 17 wherein the gas atmosphere comprises ammonia.

20. (Previously Presented) The epitaxial growth method of claim 17 wherein the gas atmosphere comprises radical nitrogen atoms.

21. (Withdrawn) The epitaxial growth method of claim 16 wherein the spin-coated film is selected from the group consisting of GaN, AlN, InGaN, and AlGaN.